

BCV62

PNP general-purpose double transistors

Rev. 4 — 26 July 2010

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		NPN complement
	Nexperia	JEITA	
BCV62	SOT143B	-	BCV61
BCV62A			BCV61A
BCV62B			BCV61B
BCV62C	_		BCV61C

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-100	mΑ
Transisto	r TR1					
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	100	-	-	
		$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$	100	-	800	



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 Table 2.
 Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Transistor	TR2					
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$				
	BCV62		100	-	800	
	BCV62A		100			
	BCV62B		220	-	475	
	BCV62C		420	-	800	

2. Pinning information

Table 3. Pinning

Table 3.	rinning		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2	4 3	4 3
2	collector TR1		
3	emitter TR1		TR2
4	emitter TR2	1 2	1 2
			006aaa843

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
BCV62	· -	plastic surface-mounted package; 4 leads	SOT143B			
BCV62A						
BCV62B						
BCV62C						

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BCV62	3M*
BCV62A	3J*
BCV62B	3K*
BCV62C	3L*

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• •	•		
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
V_{CBO}	collector-base voltage	open emitter	-	-30	V
V_{CEO}	collector-emitter voltage	open base	-	-30	V
V _{EBS}	emitter-base voltage	$V_{CE} = 0 V$	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I_{BM}	peak base current		-	-200	mA
Per device	ce				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C
·		·	·	•	· · · · · · · · · · · · · · · · · · ·

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

^[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 8. Characteristics

 $T_i = 25$ °C unless otherwise specified.

•						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Transistor	TR1					
I _{CBO}	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 \text{ °C}$	-	-	-5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$	100	-	-	
		$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$	100	-	800	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-75	-300	mV
		$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$	-	-250	-650	mV

3CV62

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Table 8. Characteristics ...continued $T_i = 25$ °C unless otherwise specified.

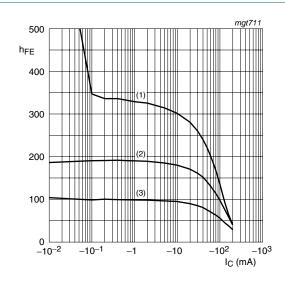
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{BEsat}	base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	<u>[1]</u> -	-700	-	mV
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	<u>[1]</u> -	-850	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	<u>[2]</u> –600	-650	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	[2] _	-	-820	mV
f _T	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	100	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}$	-	4.5	-	pF
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -200 \mu\text{A}; R_{S} = 2 \text{ k}\Omega;$ f = 1 kHz; B = 200 Hz	-	-	10	dB
Transisto	r TR2					
V _{EBS}	emitter-base voltage	$V_{CB} = 0 \text{ V}; I_{E} = -250 \text{ mA}$		-	-1.5	V
		V_{CB} = 0 V; I_E = -10 μA	-400	-	-	mV
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -2 \text{ mA}$				
	BCV62		100	-	800	
	BCV62A		100	-	250	
	BCV62B		220	-	475	
	BCV62C		420	-	800	
Transisto	rs TR1 and TR2					
I_{C1}/I_{E2}	current matching	$I_{E2} = -0.5 \text{ mA};$ $V_{CE1} = -5 \text{ V};$				
		$T_{amb} \le 25 ^{\circ}C$	0.7	-	1.3	
		T _{amb} ≤ 150 °C	0.7	-	1.3	
I _{E2}	emitter current 2	$V_{CE1} = -5 \text{ V}$	[3]	-	-5	mΑ

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] Device, without emitter resistors, mounted on an FR4 PCB.

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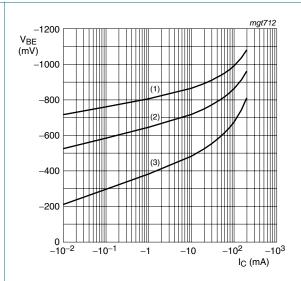
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. BCV62A: DC current gain as a function of collector current; typical values



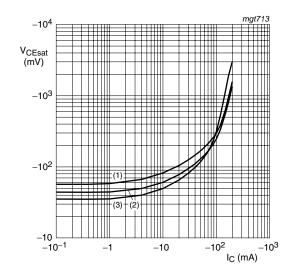
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 2. BCV62A: Base-emitter voltage as a function of collector current; typical values



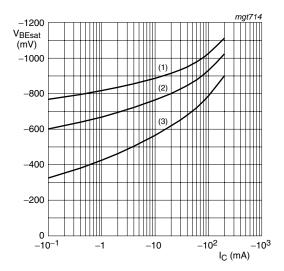
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. BCV62A: Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

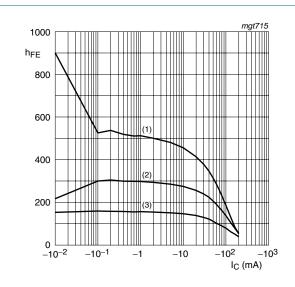
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. BCV62A: Base-emitter saturation voltage as a function of collector current; typical values

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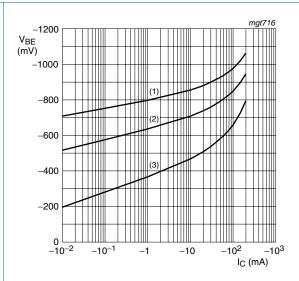
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. BCV62B: DC current gain as a function of collector current; typical values



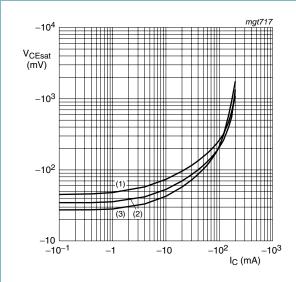
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. BCV62B: Base-emitter voltage as a function of collector current; typical values



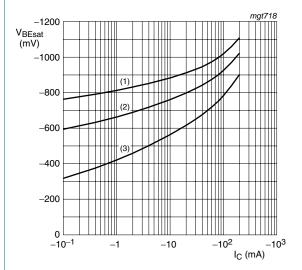
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. BCV62B: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

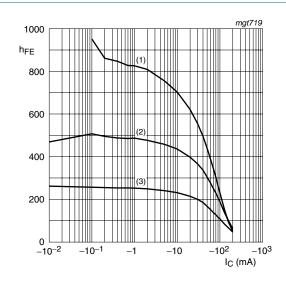
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 8. BCV62B: Base-emitter saturation voltage as a function of collector current; typical values

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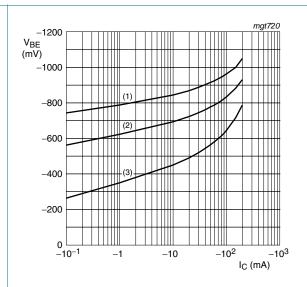
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. BCV62C: DC current gain as a function of collector current; typical values



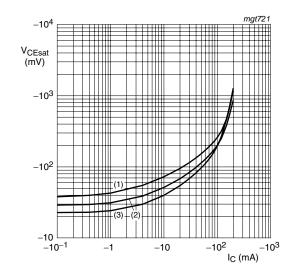
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. BCV62C: Base-emitter voltage as a function of collector current; typical values



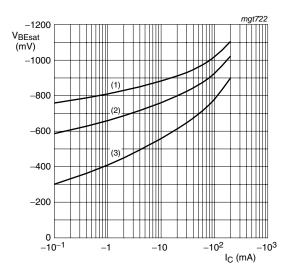
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. BCV62C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

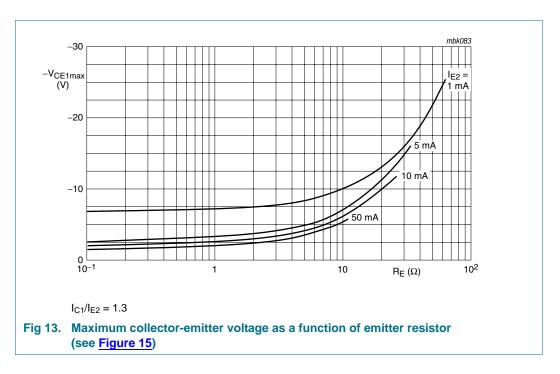
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

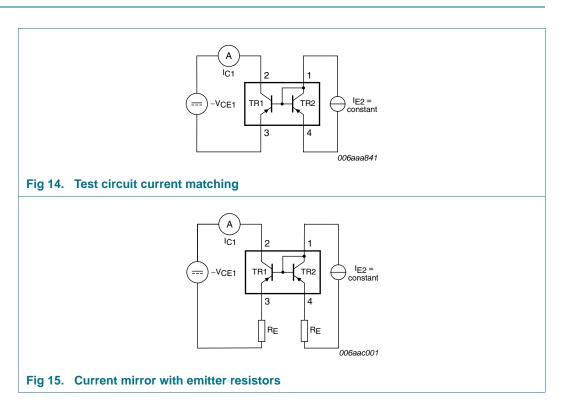
(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 12. BCV62C: Base-emitter saturation voltage as a function of collector current; typical values

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8. Test information

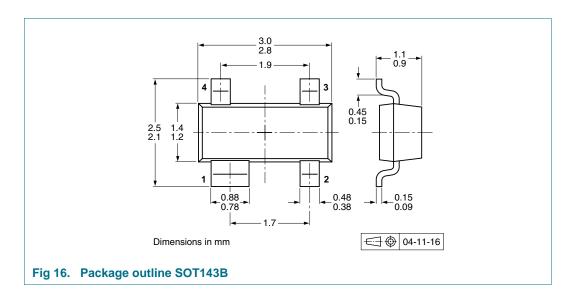


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8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

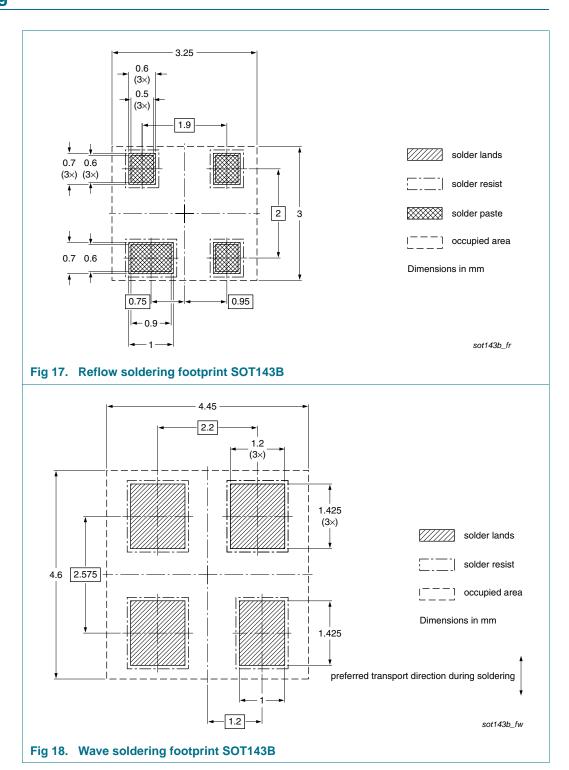
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	10000	
BCV62	SOT143B	SOT143B 4 mm pitch, 8 mm tape and reel	-215	-235	
BCV62A					
BCV62B					
BCV62C					

^[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BCV62 v.4	20100726	Product data sheet	-	BCV62_3			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	 Legal texts have been adapted to the new company name where appropriate. 						
	Section 1 "Product profile": amended						
	 Section 3 "Ordering information": added 						
	Section 4 "Marking": updated						
	• Figure 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 and 12: added						
	Section 8 "	Test information": added					
	• Figure 16: superseded by minimized package outline drawing						
	Section 10	'Packing information": adde	ed				
	Section 11 '	"Soldering": added					
	Section 13	"Legal information": updated	d				
BCV62_3	19990408	Product specification	-	BCV62_CNV_2			
BCV62_CNV_2	19970618	Product specification	-	-			

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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